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Correction: The effect of recombination under short-circuit conditions on the determination of charge transport properties in nanostructured photoelectrodes

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Correction for 'The effect of recombination under short-circuit conditions on the determination of charge transport properties in nanostructured photoelectrodes' by J. Villanueva-Cab *et al.*, *Phys. Chem. Chem. Phys.*, 2016, **18**, 2303–2308.

On page 2304 of the published article, eqn (1) should be amended as shown below:

$$\frac{\partial n}{\partial t} = \frac{\partial}{\partial x} \left[D_0 (n/n_0)^{(1-\alpha)/\alpha} \frac{\partial n}{\partial x} \right] + G(x) - k_0 (n/n_0)^{(\beta-\alpha)/\alpha} n \quad (1)$$

In addition, Fig. 2 in the published article should be replaced with the revised version below:

Fig. 2 Diffusion coefficient as function of charge density. Comparison between measured (SLIT) values and the model predictions for three different recombination rate constants: $k_0 = 0$ ($\eta_{SS, coll} = 99.5\%$ at 1 Sun), $k_0 = 2.718 \times 10^{-3} \text{ s}^{-1}$ ($\eta_{SS, coll} = 99\%$ at 1 Sun) and $k_0 = 0.12 \text{ s}^{-1}$ ($\eta_{SS, coll} = 80\%$ at 1 Sun). When recombination takes place under short circuit conditions, the diffusion coefficient is overestimated, which can be erroneously interpreted as a trap distribution of $\alpha' = 0.333$. See the text for details.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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